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Giampiero Amato, Federico Beccaria, Federica Celegato

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Growth of strained, but stable, graphene on Co

Giampiero Amato^{1,2}, Federico Beccaria^{3,4}, and Federica Celegato²

¹ Dipartimento di Scienze e Innovazione Tecnologica, Università del Piemonte Orientale “A. Avogadro”, Viale T. Michel 11, 15121 Alessandria, Italy

² Nanoscience and Materials Division, INRIM, Strada delle Cacce 91, Torino, Italy

³ Department of Physics, University of Torino, via Pietro Giuria 1, 10125 Torino, Italy

⁴ NIS Interdepartmental Center, via Pietro Giuria 1, 10125 Torino, Italy

Abstract

Mostly single-layer graphene with enhanced mechanical stability is demonstrated over polycrystalline Co film deposited onto a SiO₂/Si substrate. Raman and electrical characterizations evidence that the continuous graphene layer can be easily transferred without the aid of any polymeric support, but preserving its quality. Better stability to the damaging action of the laser beam, as compared to the Cu-grown material is observed, together with electron mobility values in the 10⁴ cm²V⁻¹s⁻¹ range. It is suggested that most of the C atoms precipitate on surface during the first 30 °C of cooling, because of the higher activation energy of C solubility into Co respect to Ni. Tensile stress is found to originate in graphene regions grown onto Co film discontinuities. Strain in the sheet is also observed after transfer. This opens possible routes to engineer the electronic spectrum through a control of the strain during growth.

Keywords: graphene; vapor deposition; strain; precipitation

¹ Corresponding author: giampiero.amato@uniupo.it, tel. +39 011 0437903, fax. +39 02 700503462

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